

### REMARKS

Claim 22 has been amended to remove the indefinite feature contained therein. Claims 22, 24 to 26 and 28 to 31 remain active in this application of which claims 24, 28 to 31 have been allowed.

Claims 22, 25 and 26 were rejected under 35 U.S.C. 103(a) as being unpatentable over Kwag et al. (U.S. 6,232,228) in view of Lee (U.S. 6,166,671). The rejection is respectfully traversed.

It is initially noted that the concentration levels of HF and H<sub>2</sub>O<sub>2</sub> as presented in the claims is a standard concentration level of the art and has no part in the invention other than to indicate such standard concentration level.

With reference to claim 22, this claim requires the step of forming a solution by combining HF with a concentration of about 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of from about 29% to about 30% in deionized water (DIW), said solution having of a volume ratio of HF:H<sub>2</sub>O<sub>2</sub>:DIW selected from the group consisting of from about 2:1:21, 3:2:10, 3:1:10 and 1:1:30. No such specific solutions are found in Kwag et al. Or Lee and for the specific materials of the claim. Note also in Kwag et al. that none of the examples utilize HF alone as the enhancer.

Claim 25 depends from claim 22 and therefore defines patentably over the applied references for at least the reasons presented above as to claim 22.

Claim 26 relates only to the etching of TaN from a semiconductor body in semiconductor device processing and requires the step of forming a solution by combining HF with a concentration of about 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of about 29 to about 30% in deionized water wherein said forming a solution further

consists of using a volume ratio greater than 1 part HF, 1 part H<sub>2</sub>O<sub>2</sub> and 20 parts deionized water. No such etching solution is found in either of the applied references, especially with respect to the etching of TaN.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,



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